

## SIDACtor Device



The modified TO-220 Type 61 *SIDACtor* solid state protection device can be used in telecommunication protection applications that do not reference earth ground.

*SIDACtor* devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21 and K.45, IEC 60950, UL 60950, and TIA-968-A (formerly known as FCC Part 68).

### Electrical Parameters

Part Number *	V <sub>DRM</sub> Volts	V <sub>S</sub> Volts	V <sub>T</sub> Volts	I <sub>DRM</sub> μAmps	I <sub>S</sub> mAmps	I <sub>T</sub> Amps	I <sub>H</sub> mAmps	C <sub>O</sub> pF
P2000AA61	180	220	4	5	800	2.2	150	30
P2200AA61	200	240	4	5	800	2.2	150	30
P2400AA61	220	260	4	5	800	2.2	150	30
P2500AA61	240	290	4	5	800	2.2	150	30
P3000AA61	270	330	4	5	800	2.2	150	30
P3300AA61	300	360	4	5	800	2.2	150	30

\* For surge ratings, see table below.

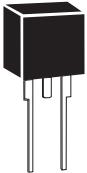
#### General Notes:

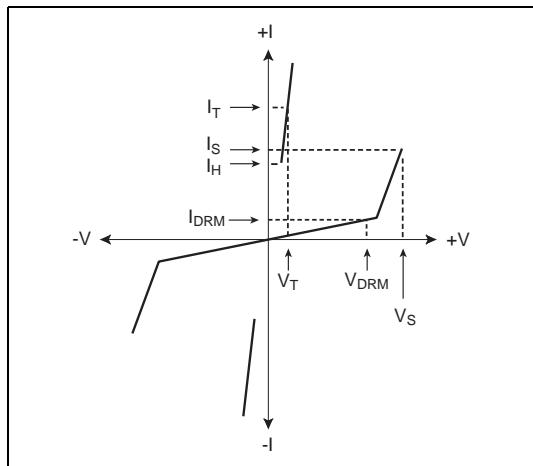
- All measurements are made at an ambient temperature of 25 °C. I<sub>PP</sub> applies to -40 °C through +85 °C temperature range.
- I<sub>PP</sub> is a repetitive surge rating and is guaranteed for the life of the product.
- Listed *SIDACtor* devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.
- V<sub>DRM</sub> is measured at I<sub>DRM</sub>.
- V<sub>S</sub> is measured at 100 V/μs.
- Special voltage (V<sub>S</sub> and V<sub>DRM</sub>) and holding current (I<sub>H</sub>) requirements are available upon request.
- Off-state capacitance (C<sub>O</sub>) is measured at 1 MHz with a 2 V bias and is a typical value.

### Surge Ratings

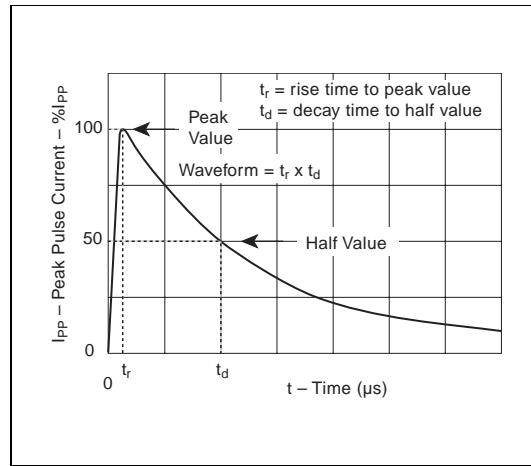
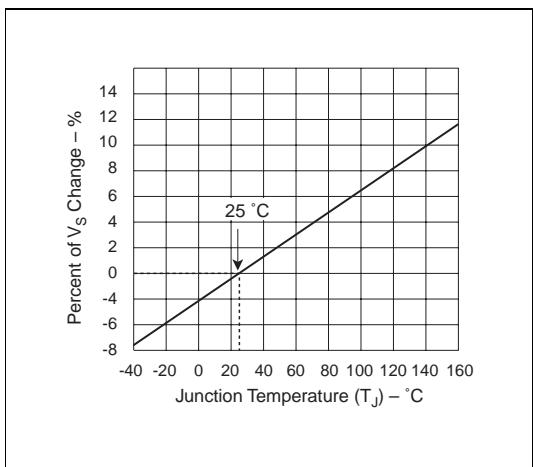
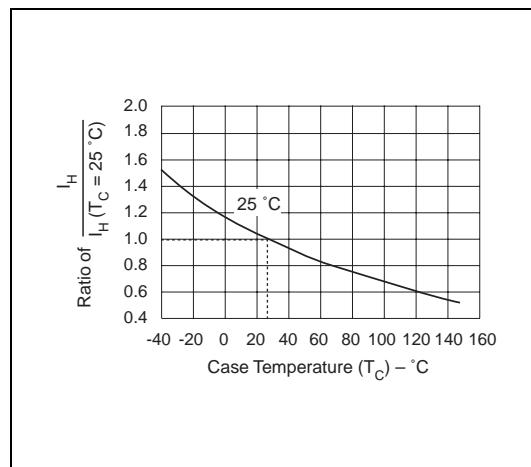
Series	I <sub>PP</sub> 0.2x310 μs Amps	I <sub>PP</sub> 2x10 μs Amps	I <sub>PP</sub> 8x20 μs Amps	I <sub>PP</sub> 10x160 μs Amps	I <sub>PP</sub> 10x560 μs Amps	I <sub>PP</sub> 5x320 μs Amps	I <sub>PP</sub> 10x1000 μs Amps	I <sub>TSM</sub> 60 Hz Amps	di/dt Amps/μs
A	20	150	150	90	50	75	45	20	500

## Thermal Considerations

Package	Symbol	Parameter	Value	Unit
Modified TO-220 Type 61		T <sub>J</sub>	Operating Junction Temperature Range	-40 to +150 °C
		T <sub>S</sub>	Storage Temperature Range	-65 to +150 °C
		R <sub>θJA</sub>	Thermal Resistance: Junction to Ambient	50 °C/W



V-I Characteristics

 $t_r \times t_d$  Pulse Wave-formNormalized  $V_S$  Change versus Junction Temperature

Normalized DC Holding Current versus Case Temperature